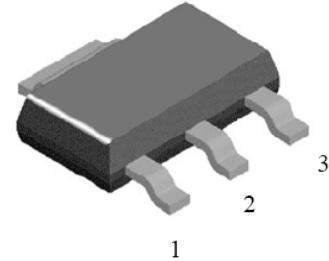


Silicon NPN bipolar Transistor

Applications:

- general amplify
- switching application.



Pin assignment

PIN NAME	PIN NUMBER	FUNCTION
	SOT-223	
B	1	BASE
C	2	COLLECTOR
E	3	EMITTER

Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ Unless Otherwise noted

PARAMETER	SYMBLE	MAXIMUM VALUE	UNIT
Collector-base breakdown voltage	VCBO	60	V
Collector-emitter breakdown voltage	VCEO	40	V
Emitter-base breakdown voltage	VEBO	6	V
Collector current	IC	0.2	A
Collector Power Dissipation	PD	0.625	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ +150 °C	°C

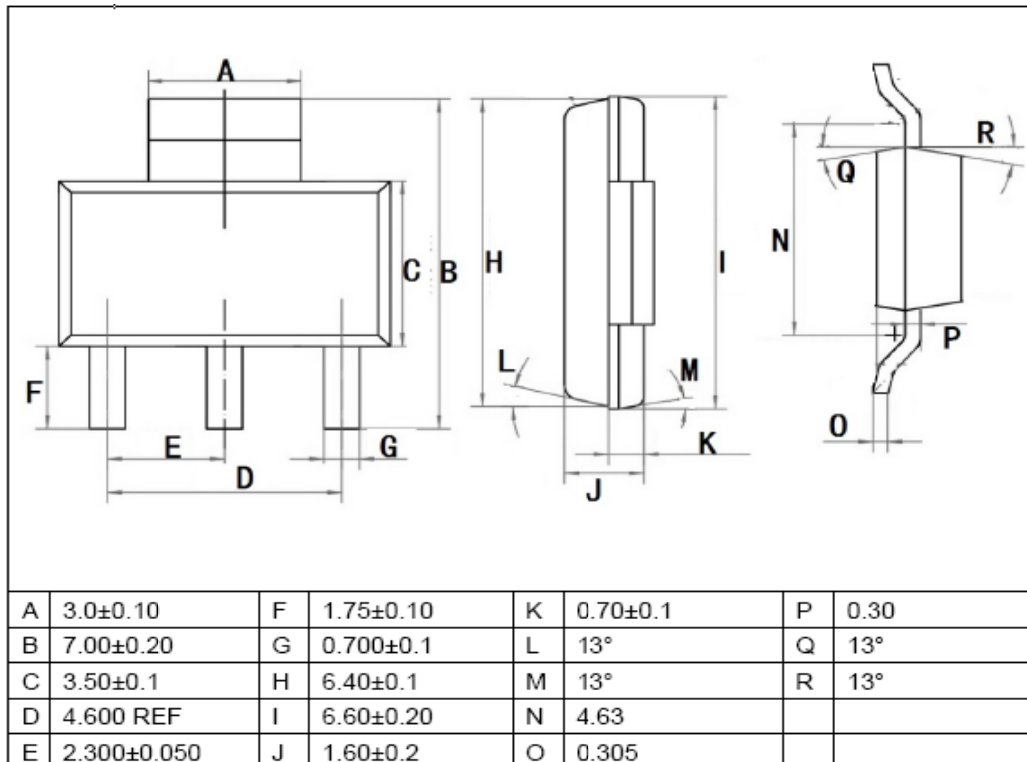
DEVICE MARKING

Marking	3904
Value	100~300

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

PARAMETER	SYMBLE	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector cut-off current	ICBO			0.05	μA	V _{CB} =50V, I _E =0
Emitter cut-off current	IEBO			0.05	μA	V _{EB} =5V, I _C =0
Collector-base breakdown voltage	V(BR)CBO	60			V	I _C =10uA, I _E =0
Collector-Emitter Breakdown Voltage	V(BR)CEO	40			V	I _C =1mA, I _B =0
Emitter-Base Breakdown Voltage	V(BR)EBO	6			V	I _E =10uA, I _C =0
DC current gain	hFE*	100		300		V _{CE} =1V, I _C =10mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.3	V	I _C =50mA, I _B =5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			0.95	V	I _C =50mA, I _B =5mA
Gain Bandwidth	f _T	300			MHz	V _{CE} =20V, I _C =10mA, f=100MHz
Cob	Cob			4	pF	V _{CB} =5V, I _E =0, f=1MHz

SOT-223 DIMENSION (Unit: mm)



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)